

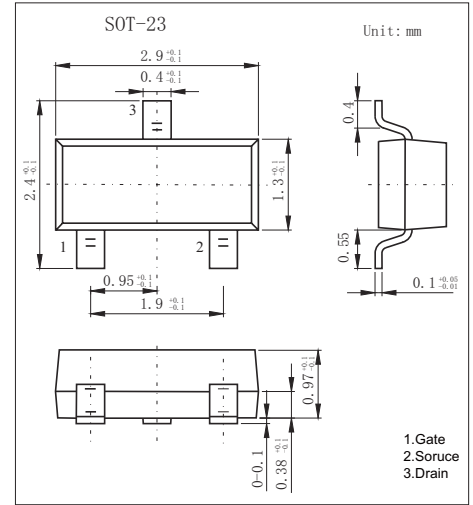
SOT-23 Plastic-Encapsulate MOSFETS

FEATURE

- Excellent RDS(ON), low gate charge,low gate voltages
- P-Channel 20-V(D-S) MOSFET

MECHANICAL DATA

- Case style:SOT-23molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	±8	
Continuous Drain Current (t≤10s)	I_D	-4.0	A
Maximum Power Dissipation (t≤10s)	P_D	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55 ~+150	°C

$V_{(BR)DSS}$	$R_{DS(on)MAX}$	I_D
-20 V	50mΩ@-4.5V	-4A
	60mΩ@-2.5V	
	73mΩ@-1.8V	

MOSFET ELECTRICAL CHARACTERISTICS Ta=25 °C unless otherwise specified

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
Static Parameters						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	-20			V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-0.3	-0.56	-1	V
Gate-body leakage current	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 8V$			±10	μA
		$V_{DS} = 0V, V_{GS} = \pm 4.5V$			±1	
Zero gate voltage drain current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1	μA
Drain-source on-state resistance(note1)	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -4A$		0.037	0.050	Ω
		$V_{GS} = -2.5V, I_D = -4A$		0.045	0.060	
		$V_{GS} = -1.8V, I_D = -2A$		0.056	0.073	
Forward transconductance(note2)	g_{FS}	$V_{DS} = -5V, I_D = -4A$	8			S
Body diode voltage(note2)	V_{SD}	$I_S = -1A, V_{GS} = 0V$			-1	V
Dynamic Parameters (note3)						
Input capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$		1450		pF
Output capacitance	C_{oss}			205		
Reverse transfer capacitance	C_{rss}			160		
Gate resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		6.5		Ω
Switching Parameters						
Total gate charge	Q_g	$V_{DS} = -10V, V_{GS} = -4.5V, I_D = -4A$		17.2		nC
Gate-Source charge	Q_{gs}			1.3		
Gate-drain charge	Q_{gd}			4.5		
Turn-on delay time (note3)	$t_{d(on)}$	$V_{DS} = -10V, V_{GS} = -4.5V$ $R_{GEN} = 3\Omega, R_L = 2.5\Omega,$		9.5		ns
Turn-on rise time(note3)	t_r			17		
Turn-off delay time(note3)	$t_{d(off)}$			94		
Turn-off fall time(note3)	t_f			35		

Notes:

1. Repetitive rating,pulse width limited by junction temperature.
2. Pulse Test : Pulse width ≅ 300μs, duty cycle ≅ 2%.
3. These parameters have no way to verify.

Typical Characteristics

